

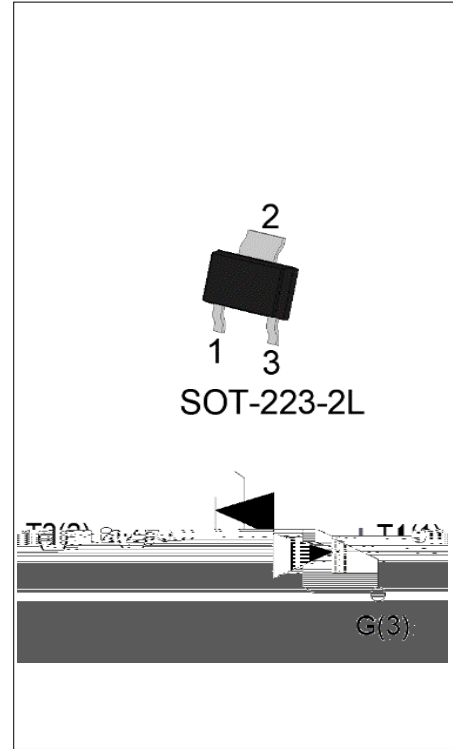


ACJT105-6W 1A TRIAC

Rev.A.1.0

DESCRIPTION:

The ACJT105-6W triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The ACJT105-6W embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. Package SOT-223-2L is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM}/V_{RRM}	600	V
$I_{GT} / /$	5/5/5	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	600	V
RMS on-state current ($T_c = 90^\circ C$)	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current (full cycle, $t_p=20ms$, $T_j=25^\circ C$)	I_{TSM}	15	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6ms$, $T_j=25^\circ C$)		16.5	
I^2t value for fusing ($t_p=10ms$, $T_j=25^\circ C$)	I^2t	1.25	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100Hz$, $T_j=125^\circ C$)	di/dt	50	$A/\mu s$
Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	2	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	0.1	W
Peak gate power	P_{GM}	5	W

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	3.5	kV
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ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	5	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3K$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	10	mA
				20	
I_H	$I_T=100mA$		MAX.	10	mA
dV/dt	$V_D=400V$ Gate Open $T_j=125$		MIN.	700	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=10V/\mu s$, $T_j=125$		MIN.	0.5	A/ms
t_{on}	$I_G=10mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	2	μs
t_{off}				20	
V_{CL}	$I_{CL}=0.1mA$ $t_p=1ms$		MIN.	700	V

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=1.1A$ $t_p=380\mu s$	$T_j=25$	1.4	V
V_{TO}	Threshold voltage	$T_j=125$	0.8	V

R_D Dynamic resistance ≈ 0.004 T_c -0.002 T_w 2j4 32a f 56.88 30 T_d <021D>n

FIG.1 Maximum power dissipation versus RMS on-state current

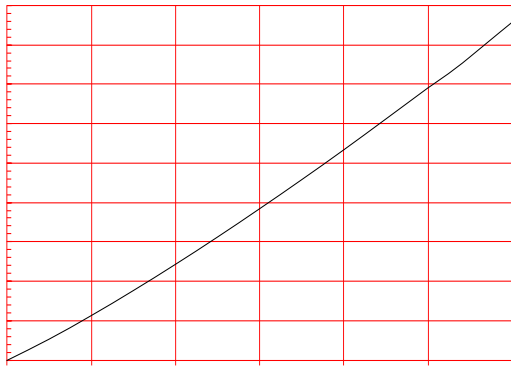


FIG.2: RMS on-state current versus case temperature

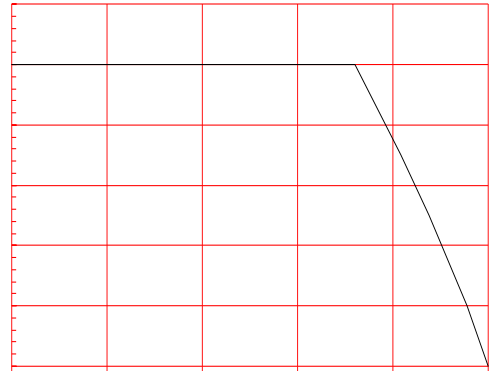


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35μm)(full cycle)

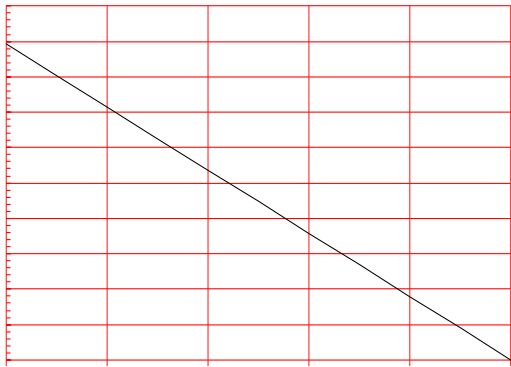


FIG.4: Surge peak on-state current versus number of cycles

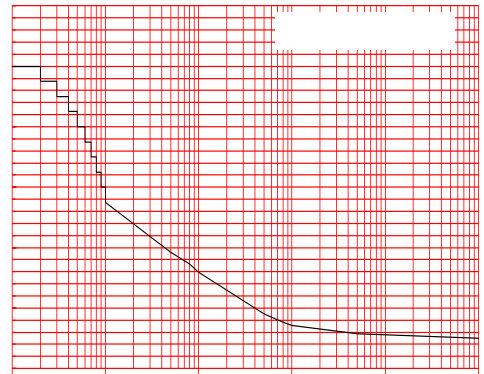


FIG.5: On-state characteristics

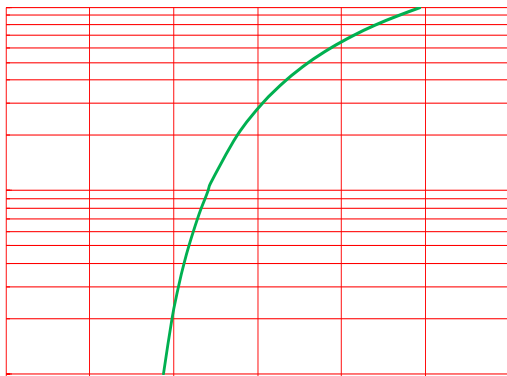


FIG.6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

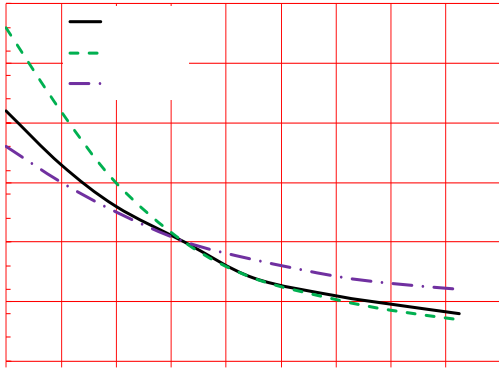
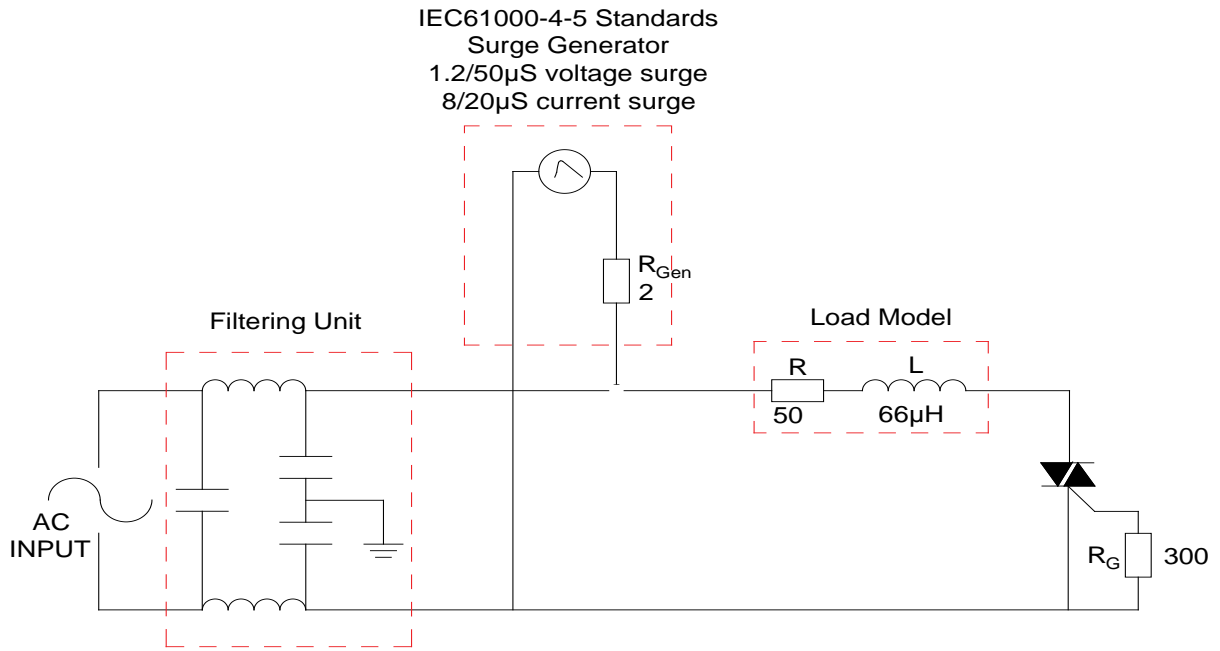


FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



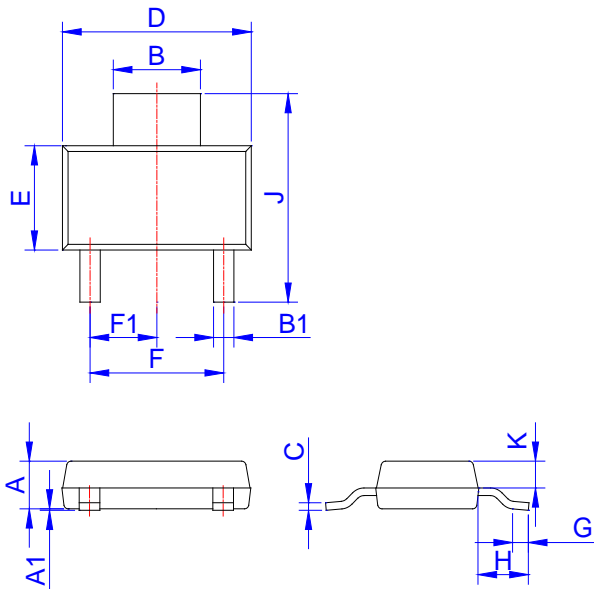
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJT105-6W	600	5	SOT-223-2L	4,000	Tape & Reel

Document Revision History

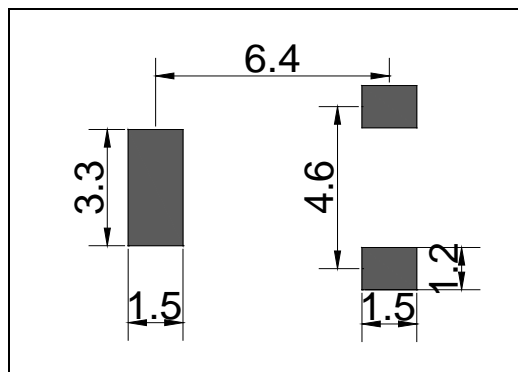
Date	Revision	Changes
Apr.13, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA




Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.50	1.60	1.80	0.059	0.063	0.071
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	2.90	3.00	3.10	0.114	0.118	0.122
B1	0.60	0.70	0.80	0.024	0.028	0.031
C	0.22	0.254	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
E	3.30	3.50	3.70	0.130	0.138	0.146
F	4.40		4.80	0.173		0.189
F1	2.20		2.40	0.087		0.094
G	0.50		1.00	0.020		0.039
H	1.50	1.75	2.00	0.059	0.069	0.079
J	6.70	7.00	7.30	0.264	0.276	0.287
K	0.80		1.00	0.031		0.039

FOOTPRINT-SOT-223-2L (dimensions in mm)



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